290-660

BDT91
BDT93
BDT95

SILICON EPITAXIAL BASE POWER TRANSISTORS

N-P-N transistors in a plastic envelope intended for use in audio output stages and general amplifier and switching applications.
P-N-P complements are BDT92, BDT94 and BDT96.

QUICK REFERENCE DATA

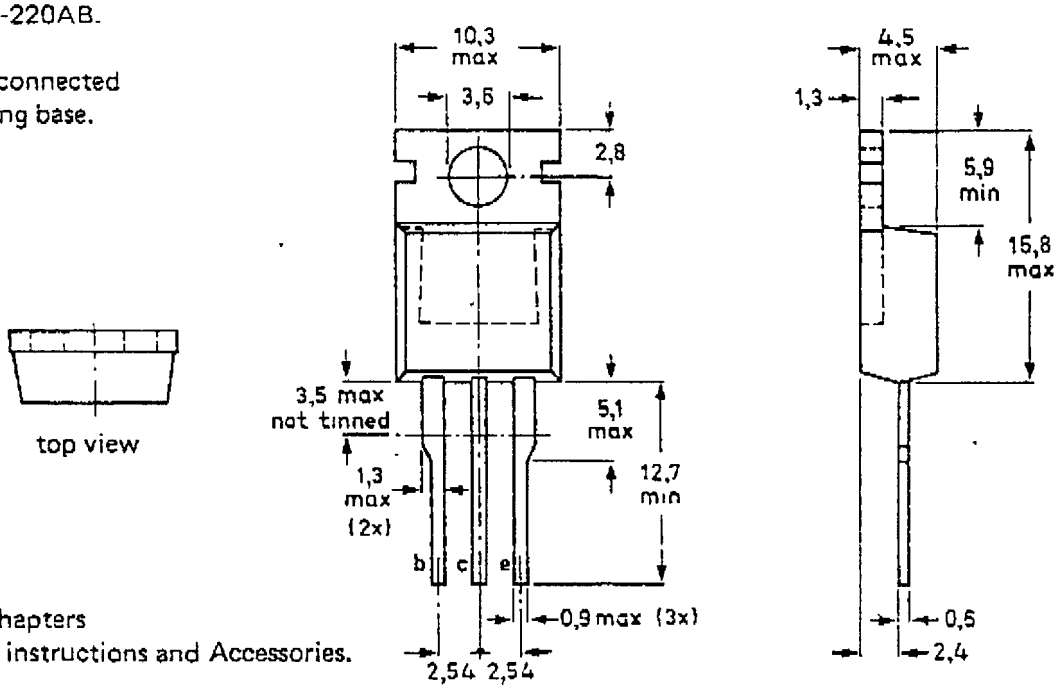
			BDT91	BDT93	BDT95	
Collector-base voltage (open emitter)	V_{CBO}	max.	60	80	100	V
Collector-emitter voltage (open base)	V_{CEO}	max.	60	80	100	V
Collector current (d.c.)	I_C	max.		10		A
Collector current (peak value)	I_{CM}	max.		20		A
Total power dissipation up to T_{mb} = 25 °C	P_{tot}	max.		90		W
Junction temperature	T_j	max.		150		°C
D.C. current gain						
I_C = 4 A; V_{CE} = 4 V	h_{FE}			20 to 200		
I_C = 10 A; V_{CE} = 4 V	h_{FE}	>		5		
Transition frequency						
I_C = 0,5 A; V_{CE} = 10 V	f_T	>		4		MHz

MECHANICAL DATA

Dimensions in mm

Fig. 1 TO-220AB.

Collector connected to mounting base.



See also chapters Mounting instructions and Accessories.

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RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

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Collector-base voltage (open emitter)	V_{CBO}	max.	60	80	100	V
Collector-emitter voltage (open base)	V_{CEO}	max.	60	80	100	V
Emitter-base voltage (open collector)	V_{EBO}	max.		7		V
Collector current (d.c.)	I_C	max.		10		A
Collector current (peak value)	I_{CM}	max.		20		A
Base current (d.c.)	I_B	max.		4		A
Total power dissipation up to T_{mb} = 25 °C	P_{tot}	max.		90		W
Storage temperature	T_{stg}			−65 to +150		°C
Junction temperature	T_j	max.		150		°C

THERMAL RESISTANCE

From junction to mounting base	$R_{th\ j\text{-}mb}$	=	1,4	K/W
From junction to ambient (in free air)	$R_{th\ j\text{-}a}$	=	70	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
I_E = 0; V_{CB} = V_{CBOmax}	I_{CBO}	<	0,1	mA
I_E = 0; V_{CB} = ½V_{CBOmax}; T_j = 150 °C	I_{CBO}	<	5	mA
I_B = 0; V_{CE} = V_{CEOmax}	I_{CEO}	<	1	mA
Emitter cut-off current				
I_C = 0; V_{EB} = 7 V	I_{EBO}	<	1	mA
D.C. current gain (note 1)				
I_C = 4 A; V_{CE} = 4 V	h_{FE}		20 to 200	
I_C = 10 A; V_{CE} = 4 V	h_{FE}	>	5	
Base-emitter voltage (notes 1 and 2)				
I_C = 4 A; V_{CE} = 4 V	V_{BE}	<	1,6	V
Collector-emitter saturation voltage (note 1)				
I_C = 4 A; I_B = 0,4 A	V_{CEsat}	<	1	V
I_C = 10 A; I_B = 3,3 A	V_{CEsat}	<	3	V
Transition frequency at f = 1 MHz				
I_C = 0,5 A; V_{CE} = 10 V	f_T	>	4	MHz
Cut-off frequency				
I_C = 0,5 A; V_{CE} = 10 V	f_{hfe}	>	20	kHz

Notes

1. Measured under pulse conditions: $t_p \leq 300\ \mu s$, $\delta \leq 2\%$.
2. V_{BE} decreases by about 2,3 mV/K with increasing temperature.

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Second-breakdown collector current			
V_{CE} = 60 V; t_p = 0,1 s	$I_{(SB)}$	>	1,5 A
Switching times			
(between 10% and 90% levels)			
I_{Con} = 4 A; I_{Bon} = $-I_{Boff}$ = 0,4 A			
Turn-on time	t_{on}	typ.	0,5 µs
		<	1 µs
Turn-off time	t_{off}	typ.	2 µs
		<	4 µs

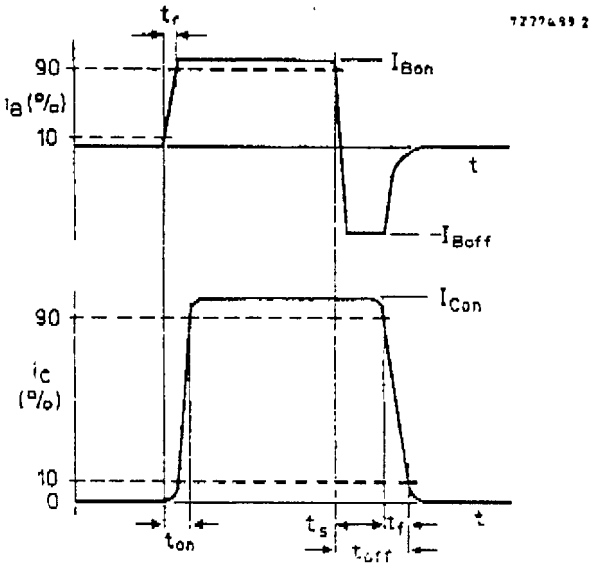
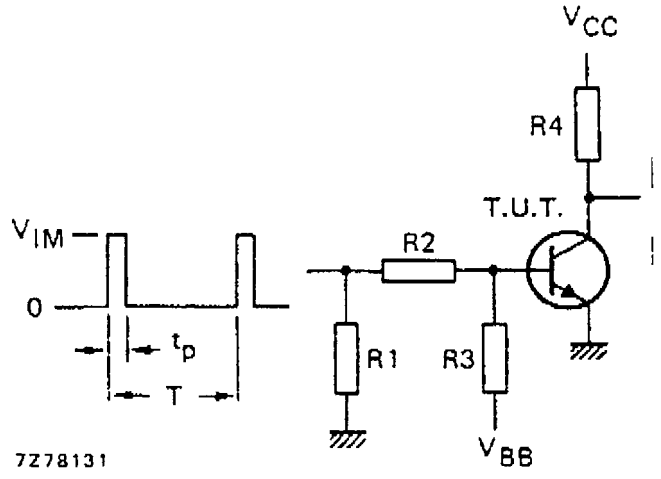


Fig. 2 Switching times waveforms.



V_{IM} = 45 V
V_{CC} = 20 V
$-V_{BB}$ = 3,5 V
R1 = 210 Ω
R2 = 56 Ω
R3 = 10 Ω
R4 = 5 Ω
$t_r = t_f$ = 15 ns
t_p = 10 µs
T = 500 µs

Fig. 3 Switching times test circuit.

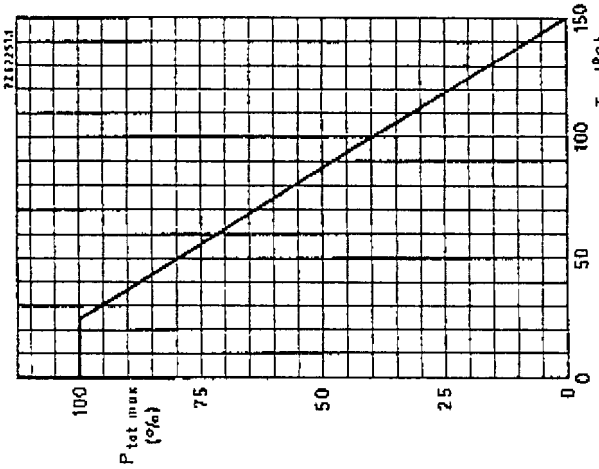


Fig. 5 Power derating curve.

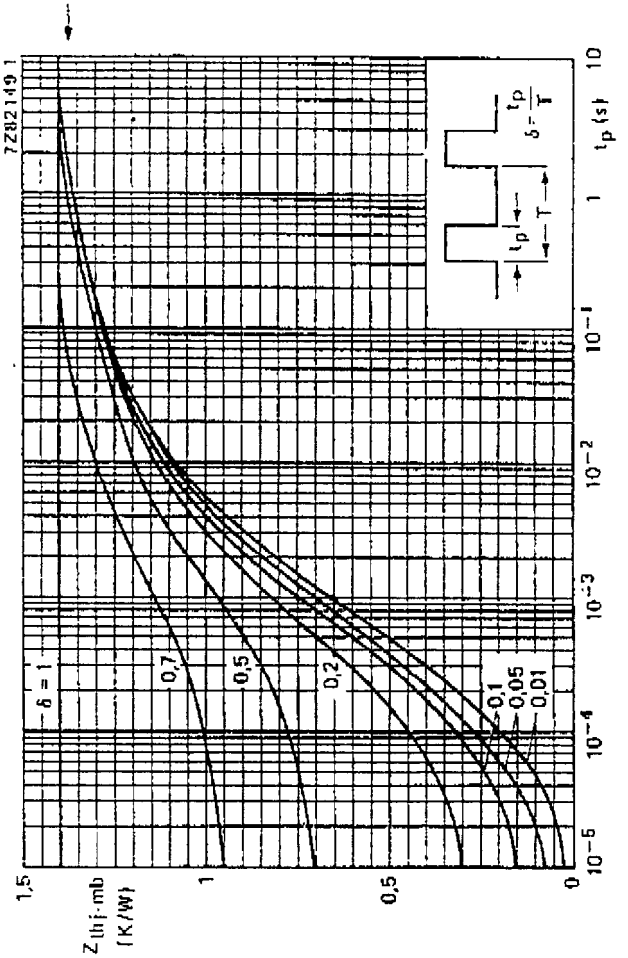


Fig. 6 Pulse power rating chart

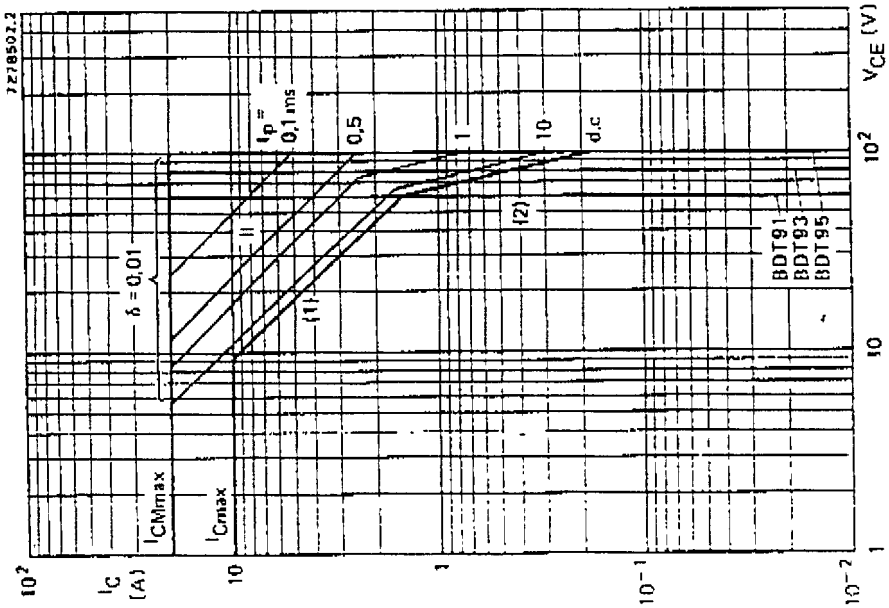


Fig. 4 Safe Operating Area; T_{mb} = 25 °C.

I Region of permissible d.c. operation.
II Permissible extension for repetitive pulse operation
(1) $P_{tot\ max}$ and $P_{peak\ max}$ lines.
(2) Second-breakdown limits (independent of temperature).

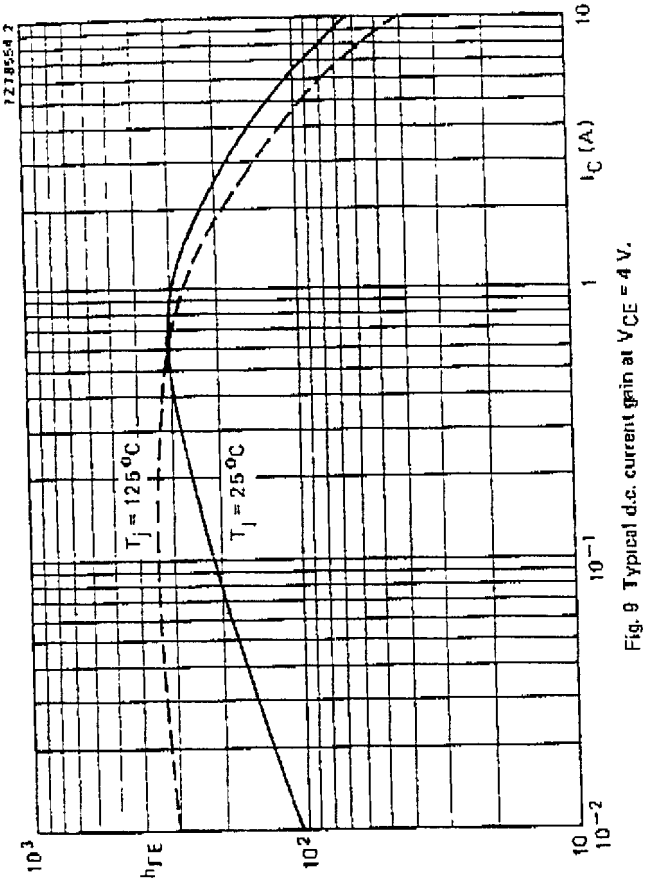


Fig. 9 Typical d.c. current gain at V_{CE} = 4 V.

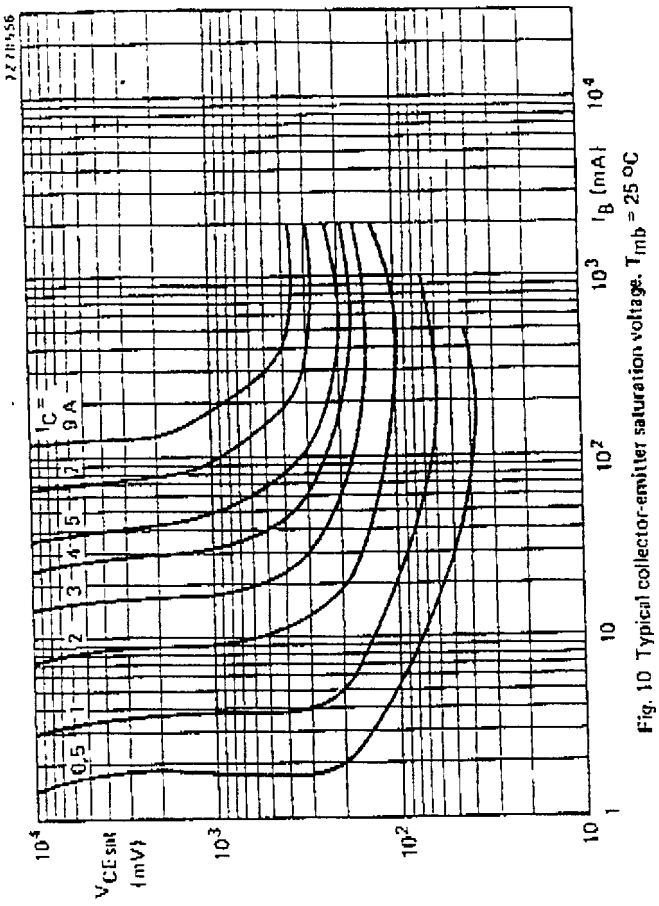


Fig. 10 Typical collector-emitter saturation voltage. T_{mb} = 25 °C

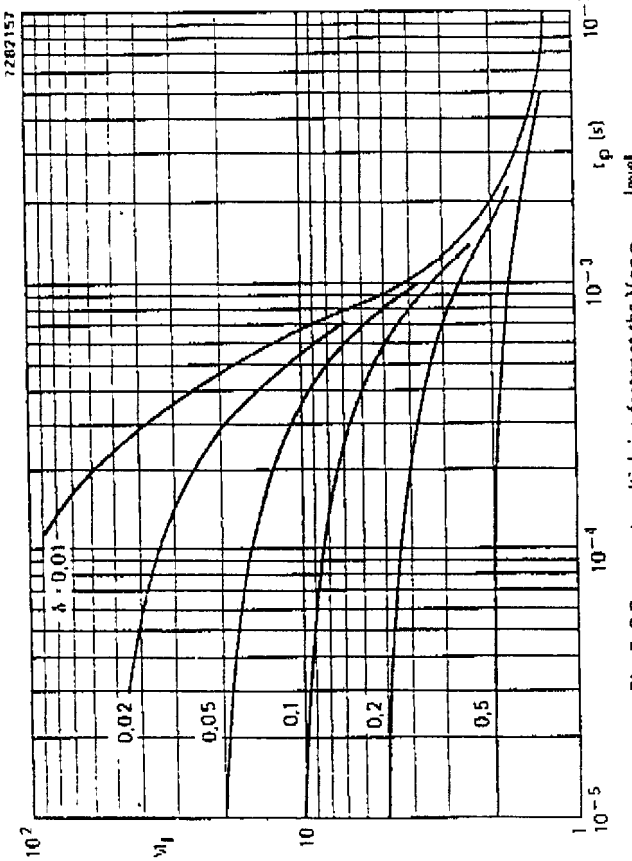


Fig 7 S.B. current multiplying factor at the V_{CEOmax} level.

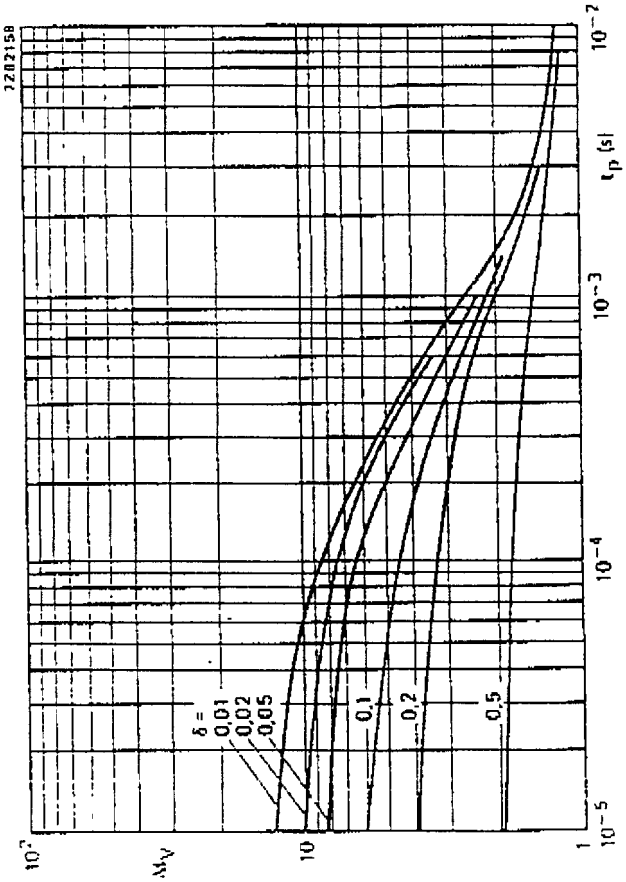


Fig 8 S.B. voltage multiplying factor at the I_{Cmax} level.